

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and as an adding element at least one element selected from the group consisting of nickel and titanium in an amount of 10 atom % or more.

2. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element at least one element selected from the group consisting of nickel and titanium in an

amount of 10 atom % or more.

3. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element titanium in an amount of 10 atom % or more.

4. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element ruthenium, and as an adding element nickel.

5. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second

capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting material at least one material selected from ruthenium oxide and iridium oxide, and as an adding element at least one element selected from the group consisting of palladium, nickel, cobalt, and titanium.

6. (original) A semiconductor device according to any one of claims 1 to 5, wherein the adding element is contained in a concentration of 10 to 25 atom %.

Claims 7-13 (cancelled)

14. (currently amended) A process for producing a semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film for a dielectric formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, which comprises forming the first capacitor electrode or the second capacitor electrode which is in contact with the insulating film by using

(a) at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium and platinum as a main constituting element and at least one element selected from the group consisting of nickel and titanium as an adding element in an amount of 10 atom % or more, or

(b) at least one material selected from the group consisting of ruthenium oxide and iridium oxide as a main constituting material, and at least one element selected from the group consisting of nickel and titanium as an

adding element in an amount of 10 atom % or more.

15. (previously presented) A process for producing a semiconductor device equipped with a capacitor for storing information comprising an oxide film formed between a first capacitor electrode and a second capacitor electrode, and an insulating film containing silicon as a main constituting element being formed for insulating one of the first capacitor electrode or the second capacitor electrode, which comprises

forming an electroconductive film containing as a main constituting element at least one element selected from the group consisting of palladium, nickel, cobalt and titanium between said one of the first capacitor electrode or the second capacitor electrode and the insulating film.

16. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising:

a first capacitor electrode;

a second capacitor electrode;

an oxide film; and

an insulating film, said insulating film being formed outside of said first capacitor electrode or said second capacitor electrode,

wherein said first capacitor electrode or said second capacitor electrode contain as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and, near the boundary of said insulating film, said first capacitor electrode or said second capacitor electrode includes a region containing an element selected from the group consisting of palladium, nickel, cobalt, and titanium in a concentration of more than about 15 atom %.

17. (previously presented) A semiconductor device equipped with a capacitor for storing information comprising a substrate, a first capacitor electrode formed on the substrate, an oxide film formed in contact with the first capacitor electrode, a second capacitor electrode formed in contact with the oxide film, and an insulating film containing silicon as a main constituting element and formed in contact with the first capacitor electrode or the second capacitor electrode, said first capacitor electrode or said second capacitor electrode which is in contact with the insulating film containing as a main constituting element at least one element selected from the group consisting of rhodium, ruthenium, iridium, osmium, and platinum, and means for enhancing adhesiveness of said first or said second capacitor electrode to said insulating film to prevent peeling comprising providing as an adding element to said first or second capacitor electrode at least one element selected from the group consisting of nickel and titanium.

18. (previously presented) A semiconductor device according to claim 17, wherein the adding element is contained in a concentration of 10 atom % or more.